



Product Summary

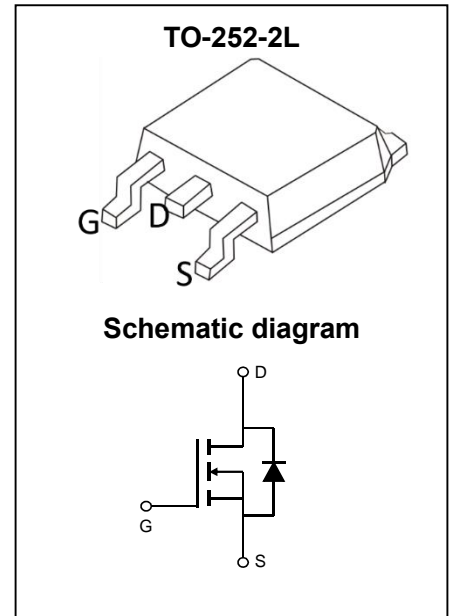
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
650V	1.2Ω@10V	7A

Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested
- 100% ΔV_{DS} Tested

Application

- Power Switching Application



MARKING:



07N65= Device Code
 XX = Date Code
 Solid Dot = Green Indicator

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	650	V
Gate - Source Voltage	V_{GS}	±30	V
Continuous Drain Current ¹	I_D	7	A
	$T_C = 25^\circ\text{C}$		
Pulsed Drain Current ²	I_{DM}	28	A
Single Pulsed Avalanche Current ³	I_{AS}	17.5	A
Single Pulsed Avalanche Energy ³	E_{AS}	76.5	mJ
Power Dissipation ⁵	P_D	54	W
	$T_C = 25^\circ\text{C}$		
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2.3	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

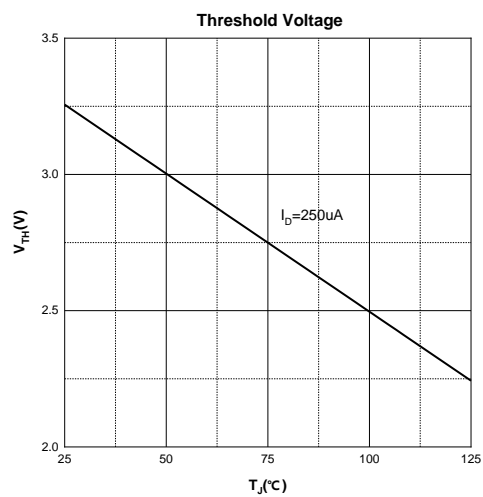
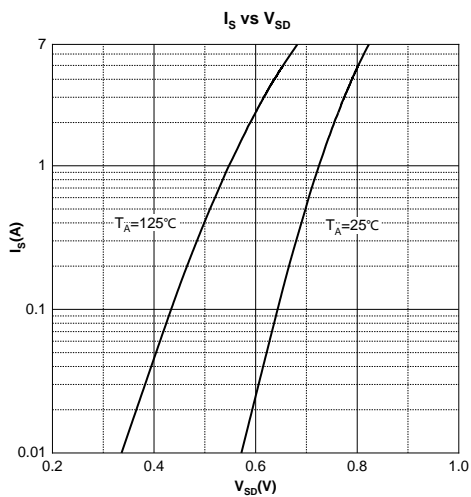
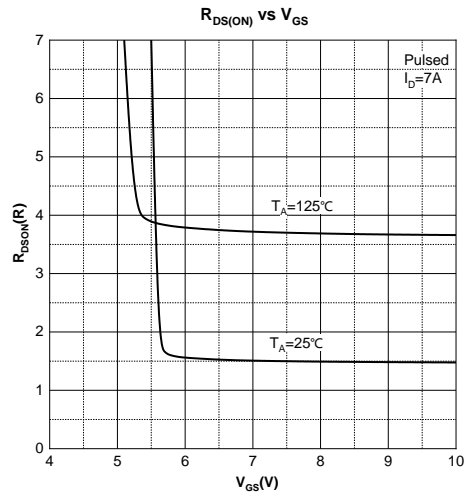
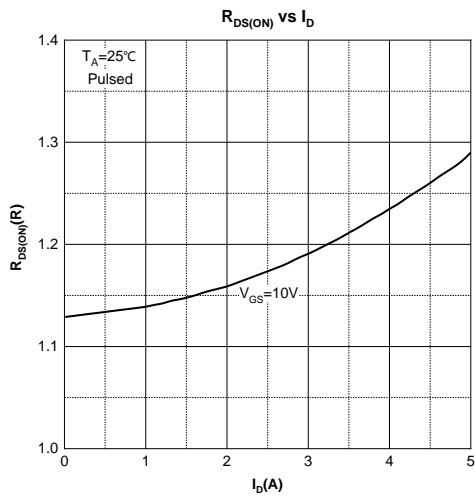
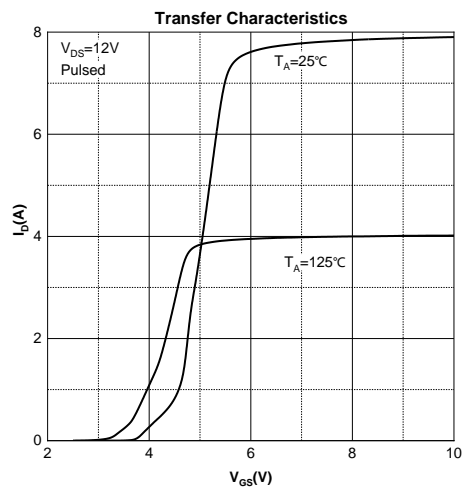
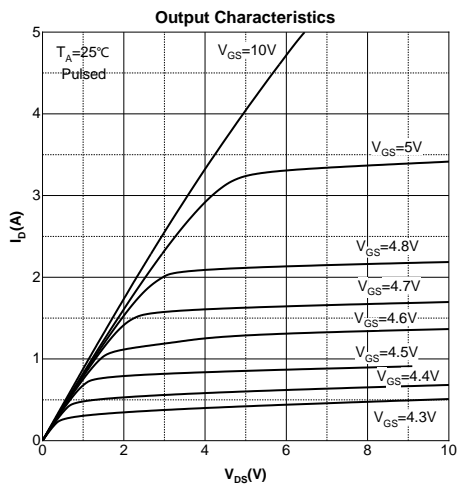
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

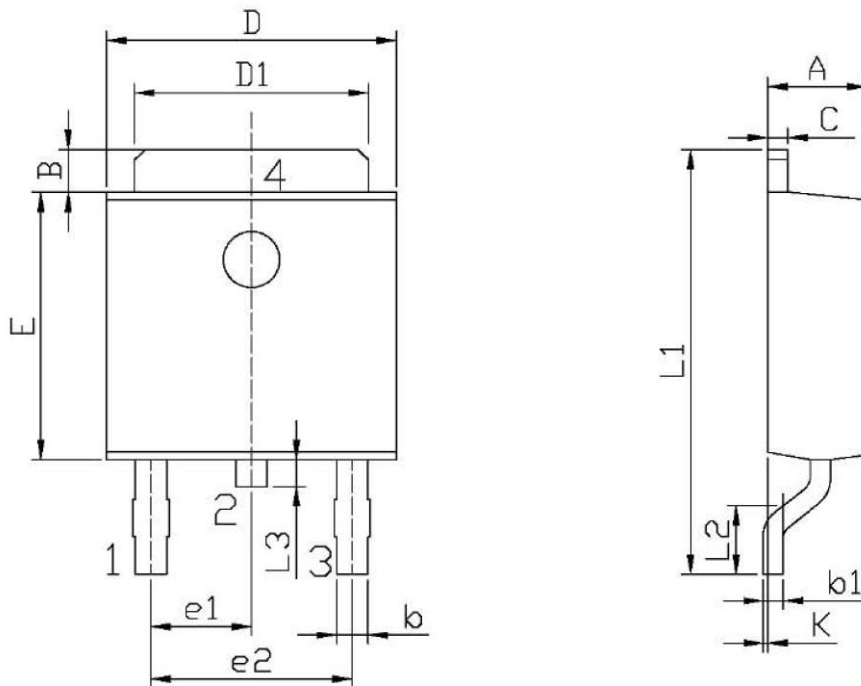
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3.2	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1A$		1.2	1.7	Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 10A$		16.5		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 45V, V_{GS} = 0V, f = 1MHz$		1170		pF
Output Capacitance	C_{oss}			63.9		
Reverse Transfer Capacitance	C_{rss}			2.6		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.1		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 335V, V_{GS} = 10V, I_D = 1A$		17.1		nC
Gate-source Charge	Q_{gs}			0.6		
Gate-drain Charge	Q_{gd}			3.6		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 2A, R_G = 25\Omega$		33.6		ns
Turn-on Rise Time	t_r			7.2		
Turn-off Delay Time	$t_{d(off)}$			64		
Turn-off Fall Time	t_f			31.2		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 2A$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 100V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



TO-252-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
B	0.950	1.250	0.037	0.049
b	0.500	0.700	0.020	0.028
b1	0.450	0.550	0.018	0.022
C	0.450	0.550	0.018	0.022
D	6.450	6.750	0.254	0.266
D1	5.100	5.500	0.201	0.217
E	5.950	6.250	0.234	0.246
e1	2.240	2.340	0.088	0.092
e2	4.430	4.730	0.174	0.186
L1	9.450	9.950	0.372	0.392
L2	1.250	1.750	0.049	0.069
L3	0.600	0.900	0.024	0.035
K	0.000	0.100	0.000	0.004